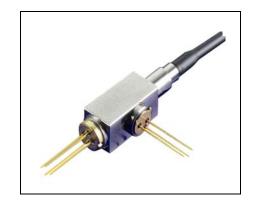


SBL52214x

Low Power BIDI[®] Optical Standard Module 1310 nm Emitting, 1310 nm Receiving

Features

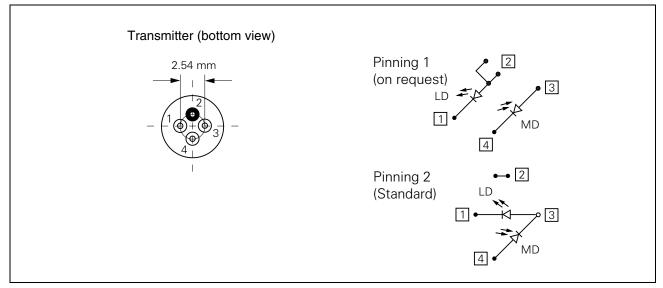
- Designed for application in passive-optical networks
- Integrated Wavelength Division Multiplexer (WDM) or Beam Splitter
- Bi-Directional Transmission in one optical window
- Single fiber solution
- FP-Laser Diode with Multi-Quantum Well structure
- Class 3B Laser Product
- Suitable for bit rates up to 1.25 Gbit/s
- Ternary Photodiode at rear mirror for monitoring and control of radiant power
- Low noise / high bandwidth PIN diode
- Hermetically sealed subcomponents, similar to TO 46
- With singlemode fiber pigtail





Pin Configuration

Pin Configuration





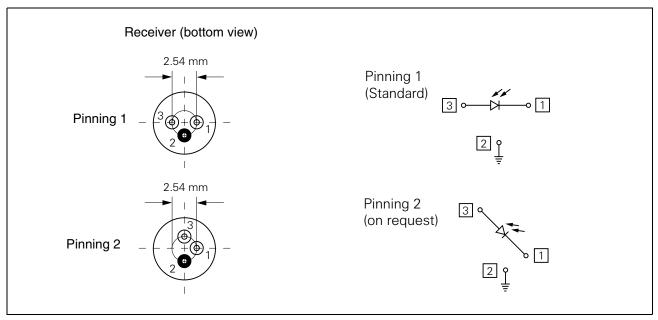


Figure 2 Receiver

Available Pinnings

Туре	Transmitter	Receiver
SBL52214x	2 (Standard)	1 (Standard)
SBL51214x	1 (on request)	1 (on request)

Other Pinnings on request / different drawing set required for non standard pinning



Description

Description

The Infineon module for bidirectional optical transmission has been designed for different optical networks structures.

In the last few years the structure has changed from point to point planned for Broad band ISDN to a point to multipoint passive optical network (PON) architecture for the optical network in the subscriber loop.

A transceiver can be realized with discrete elements (Figure 3). Transmitter and receiver with pigtails are connected with a fiber-coupler (2:1 or 2:2, wavelength independent or WDM).

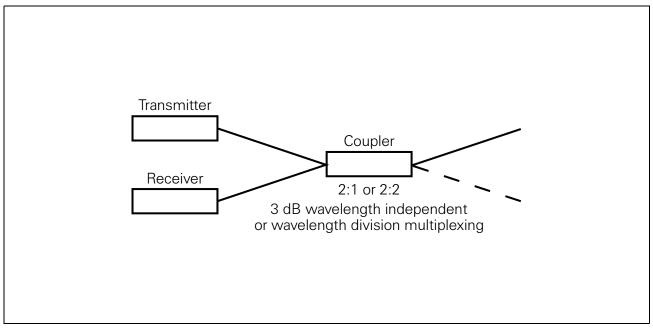


Figure 3 Realization with Discrete Elements

Infineon has realized this transceiver configuration in a compact module called a BIDI[®] (Figure 4).

This module is especially suitable for separating the opposing signals at the ends of a link. It replaces a discrete solution with a transmitter, receiver and coupler.

The basic devices are a laser diode and a photodiode, each in a TO package, plus the filter in the beam path. A lens in the TO laser concentrates the light and enables it to be launched into the single-mode fiber of the module. In the same way the light from the fiber is focused onto the small, light-sensitive area of the photodiode to produce a high photo current. The mirror for coupling out the received signal is arranged in the beam so that the transmitter and receiver are at right angles to each other. This means the greatest possible degree of freedom in the layout of the electric circuit.



SBL52214x

Description

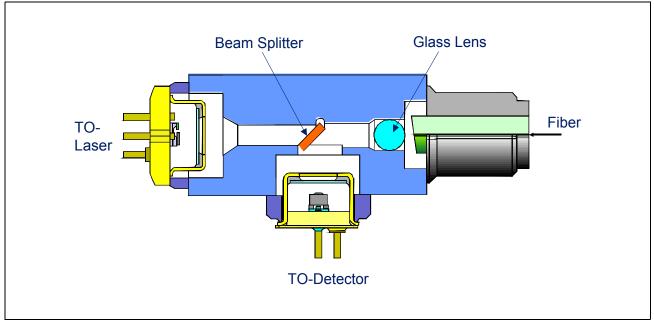


Figure 4Compact Realization of the Transceiver in One Module

A decisive advantage of the module is its use of standard TO components. These devices, produced in large quantities, are hermetically sealed and tested before they are built in. This makes a very substantial contribution to the excellent reliability of the module. The solid metal package of the module serves the same purpose. It allows the use of modern laser welding techniques for reliable fixing of the different elements and the fiber holder.



Technical Data

Technical Data

Absolute Maximum Ratings

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Module		L		
Operating temperature range at case	T _C	-40	85	°C
Storage temperature range	T_{stg}	-40	85	
Soldering temperature ($t_{max} = 10$ s, 2 mm distance from bottom edge of case)	T _S		260	
Laser Diode			·	·
Direct forward current	I _{F max}		120	mA
Radiant power CW	$P_{\rm F, rad}$		1	mW
Reverse Voltage	V_{R}		2	V
Monitor Diode			·	
Reverse Voltage	V_{R}		10	V
Forward Current	I _F		2	mA
Receiver Diode			·	
Reverse Voltage	V_{R}		10	V
Forward Current	I _F		2	mA
Optical power into the optical port	P _{port}		1.5	mW



Technical Data

The electro-optical characteristics described in the following tables are only valid for use within the specified maximum ratings or under the recommended operating conditions.

Parameter	Symbol		Limit Va	ues	Unit
		min.	typ.	max.	
Optical output power (maximum)	P _{F, max}	0.4			mW
Emission wavelength center of range, $P_{\rm F}$ = 0.5 $P_{\rm F, max.}$	λ_{trans}	1270		1350	nm
Spectral width (RMS)	σ_{λ}			5	
Temperature coefficient of wavelength	TC			0.5	nm/K
Threshold current (whole temperature range)	I _{th}	2		45	mA
Forward voltage, $P_{\rm F} = 0.5 P_{\rm F, max.}$	V_{F}			1.5	V
Radiant power at $I_{\rm th}$	P _{th}			20	μW
Slope efficiency (–4085°C)	η	8		60	mW/A
Variation of 1st derivative of P/I (0.05 to 0.4 mW)	S _{var}	-30		30	%
Differential series resistance	R _S			8	Ω
Rise time (10%–90%)	t _r		100	200	ps
Fall time (10%–90%)	t _f		270	500	

Monitor Diode Electro-Optical Characteristics

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Dark current, $V_{R} = 5 \text{ V}$, $P_{F} = 0$, $T = T_{max}$	I _R		200	nA
Photocurrent, $V_{\rm R}$ = 5 V, $P_{\rm F}$ = 0.5 $P_{\rm F, max}$	IP	50	1500	μA
Capacitance, $V_{\rm R}$ = 5 V, f = 1 MHz	<i>C</i> ₅		10	pF
Tracking error ¹ , $V_{\rm R}$ = 5 V	TE	-1	1	dB

¹⁾ The tracking error TE is the maximum deviation of $P_{\rm F}$ at constant current $I_{\rm mon}$ over a specified temperature range and relative to the reference point: $I_{\rm mon, ref} = I_{\rm mon}$ ($T = 25^{\circ}$ C, $P_{\rm F} = 0.5 P_{\rm F, max}$). Thus, TE is given by:

$$\mathsf{TE}[\mathsf{dB}] = 10 \times \log \frac{P_{\mathsf{F}}[T_{\mathsf{C}}]}{P_{\mathsf{F}}[25^{\circ}\mathsf{C}]}$$



Technical Data

Receiver Diode Electro-Optical Characteristics

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Spectral sensitivity, $V_{\rm R} = 5$ V, $\lambda = 1310$ nm	S _{rec}	0.3	1	A/W
Rise and fall time (10%–90%) $R_{\rm L}$ = 50 Ω , $V_{\rm R}$ = 5 V	$t_{\rm r}; t_{\rm f}$		1	ns
Total capacitance $V_{\rm R}$ = 5 V, $P_{\rm opt}$ = 0, f = 1 MHz	С		1.5	pF
Dark current, $V_{\rm R}$ = 5 V, $P_{\rm opt}$ = 0	ID		50	nA

Module Electro-Optical Characteristics

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Optical Crosstalk ¹⁾	CRT		-22	dB

¹⁾ Optical Crosstalk is defined as

 $CRT[dB] = 10 \times \log \frac{I_{Det.0}}{I_{Det.1}}$

with: $I_{\text{Det},0}$: the photocurrent with $P_{\text{F}} = 0.5 P_{\text{F, max.}}$, without optical input, CW laser operation, $V_{\text{R}} = 2 \text{ V}$ and $I_{\text{Det},1}$: the photocurrent without P_{F} , but 0.5 $P_{\text{F, max.}}$ optical input power, $\lambda = 1310 \text{ nm.}$

End of Life Time Characteristics

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Threshold current at $T = T_{max}$	I _{th}		60	mA
Current above threshold, over full temperature range, at $I_{\text{mon, ref}} = I_{\text{mon}}$ ($T = 25^{\circ}$ C, $P_{\text{F}} = 0.5 P_{\text{F, max}}$, BOL)	ΔI_{F}	7	70	
Tracking Error	TE	-1.5	1.5	dB
Detector Dark Current, $V_{\rm R}$ = 2 V, $T = T_{\rm max}$	I _R		400	nA
Monitor Dark Current, $V_{R} = 2 V$, $T = T_{max}$	I _R		1	μA



Fiber Data

Fiber Data

The mechanical fiber characteristics are described in the following table.

Fiber Characteristics

Parameter	Limit Values			
	min.	typ.	max.	
Mode Field Diameter	8	9	10	μm
Cladding Diameter	123	125	127	
Mode Field/Cladding Concentricity Error			1	
Cladding Non-circularity			2	%
Mode Field Non-circularity			6	
Cut off Wavelength	1270			nm
Jacket Diameter	0.8		1	mm
Bending Radius	30			
Tensile Strength Fiber Case	5			Ν
Length	0.8		1.2	m



Eye Safety

Eye Safety

Ensure to avoid exposure of human eyes to high power laser diode emitted laser beams. Especially do not look directly into the laser diode or the collimated laser beam when the diode is activated.

Class 3B Laser Product According to IEC 60825-1

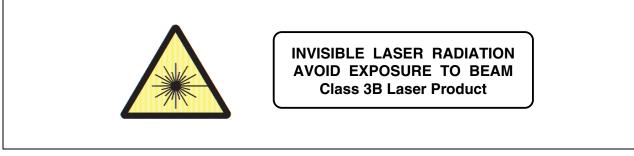


Figure 5 Required Labels

Class IIIb Laser Product According to FDA Regulations Complies with 21 CFR 1040.10 and 1040.11

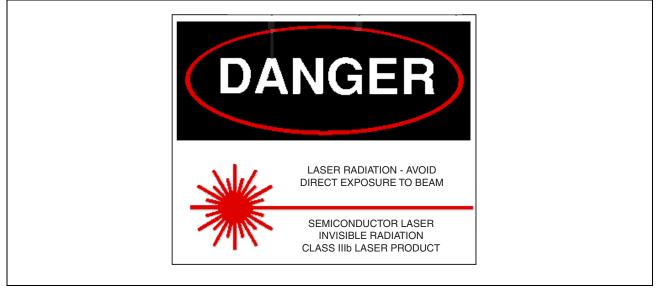


Figure 6 Required Label

Laser Data

Wavelength	1310 nm
Maximum total output power	less than 50 mW
Beam divergence (1/e ²)	10°



Package Outlines

Package Outlines

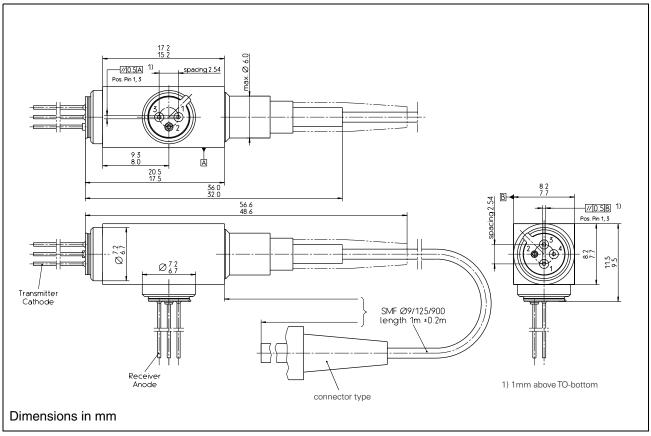


Figure 7

Connector Options

Model	Туре
SBL52214G SBL51214G	SM FC/PC
SBL52214N SBL51214N	SM SC/PC 0°
SBL52214Z SBL51214Z	SM without connector

SBL5221	14x		
Revision	n History:	2002-05-01	DS0
Previous	Version:		
Page	Subjects	(major changes since last revision)	
	Documen	t's layout has been changed: 2002-Aug.	

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